Desert Silicon
LIQUID SOURCE SOLUTIONS

Spin-on-Glass GaAl-330

Elements of Interest	Key Element atoms/cm^3	Key Element % in Film
Si, O, Ga, Al	Ga, 4E+21, Al, 9.4E+21	Gallium, Aluminum
Viscosity, n (635nm)	**Thickness**	**Shelf Life**
1.0 cps, (1.46-1.50)	Coats 200 nm at 3000 rpm	20°C 3 months 4°C 9 months

Benefits

- Gallium, Aluminum mixture
- Uniform Coatings
- High purity materials
- Lower melting point than silica alone
- Stable processing independent of flow rates
- Available with impurity specification of less than 1 ppm or less than 50 ppb

Typical Application

This is a mixture of silicate gallium and aluminum doped glass useful for semiconductor applications. It begins curing at about 200°C to give a less dense but solid film. It continues to become increasingly stronger as bakes continue to 650°C or higher. We recommend baking at the highest temperature the material will see in any post processing. For doping applications the glass is often removed after drive in.

Packaging

- 240ml
- 500ml
- 1 l
- 2.5 l
- 4 l

Alternative Products

- Ga-100
- GaB-220
- Al-250

Alternate Elements to Add

- Blends of two or more elements
- Other elements available for compound semiconductor use

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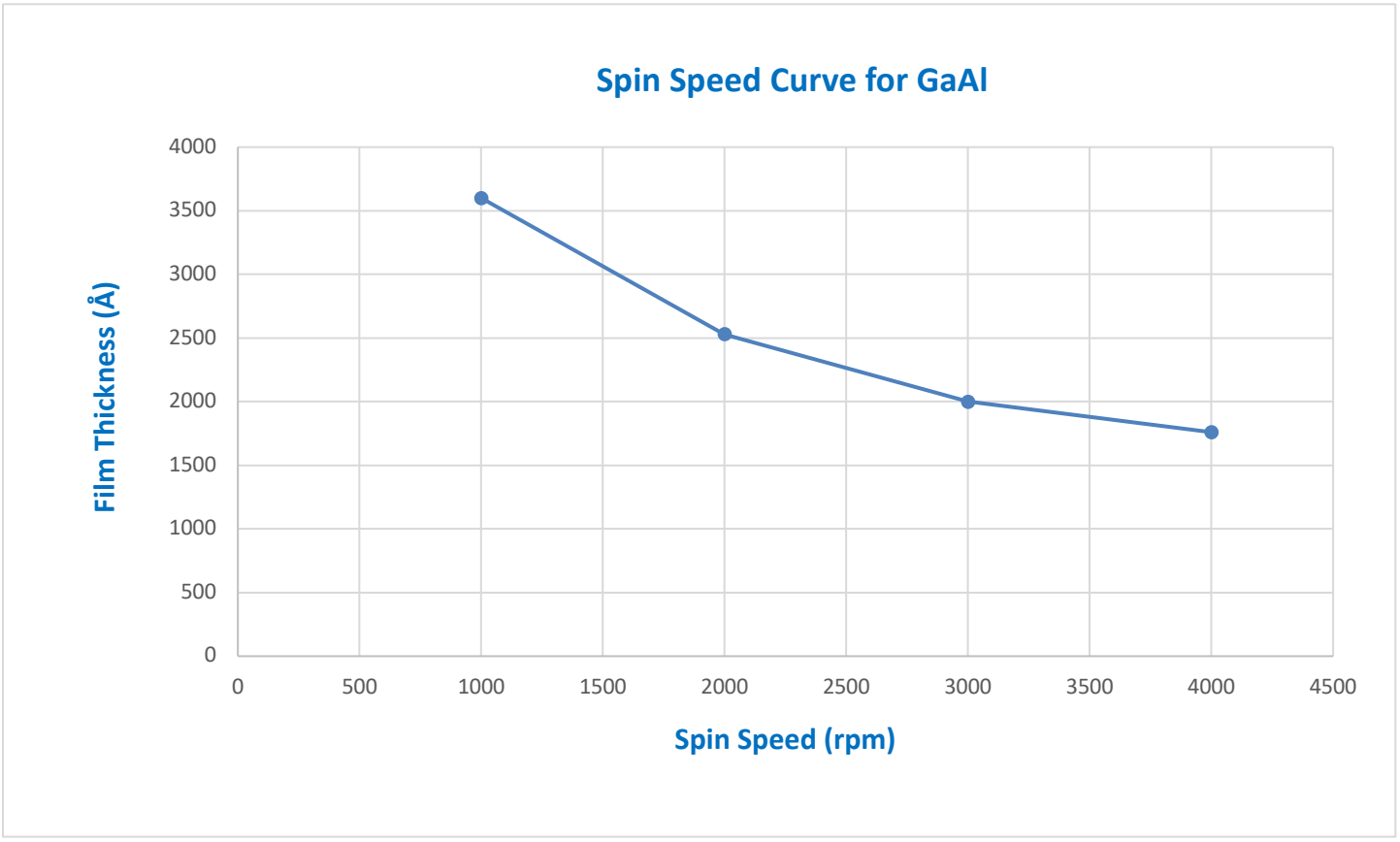

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